Document made available under the Patent Cooperation Treaty (PCT)

International application number: PCT/GB05/001709

International filing date: 04 May 2005 (04.05.2005)

Document type: Certified copy of priority document

Document details: Country/Office: US

Number: 60/572,434

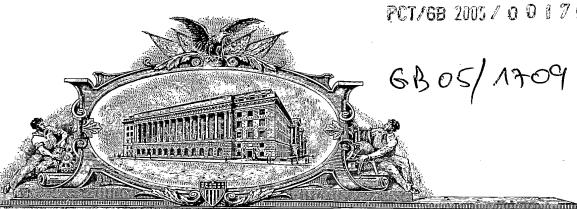
Filing date: 19 May 2004 (19.05.2004)

Date of receipt at the International Bureau: 31 May 2005 (31.05.2005)

Remark: Priority document submitted or transmitted to the International Bureau in

compliance with Rule 17.1(a) or (b)





TO ALL TO WHOM THUSD: PRESERVES SHAVE COME;

UNITED STATES DEPARTMENT OF COMMERCE

United States Patent and Trademark Office

April 01, 2005

THIS IS TO CERTIFY THAT ANNEXED HERETO IS A TRUE COPY FROM THE RECORDS OF THE UNITED STATES PATENT AND TRADEMARK OFFICE OF THOSE PAPERS OF THE BELOW IDENTIFIED PATENT APPLICATION THAT MET THE REQUIREMENTS TO BE GRANTED A FILING DATE UNDER 35 USC 111.

APPLICATION NUMBER: 60/572,434

FILING DATE: May 19, 2004

By Authority of the

COMMISSIONER OF PATENTS AND TRADEMARKS

P. SWAIN

Certifying Officer

حت
~~
·×
_

Please type a plus sign (+) inside this box -

PTO/SB/16 (5-03)
Approved for use through 04/30/2003. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCED

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

လ

PROVISIONAL APPLICATION FOR PATENT COVER SHEET This is a request for filing a PROVISIONAL APPLICATION FOR PATENT under 37 CFR 1.53(c)

			NVENTOR	R(S)		31 07 01 K 1.33(c).		
Given Name (first and middle [if any]) Family Name or S				Residence				
John Fleming	v	VALKER		United Kinge				
Additional inventors are l	being named o	on thu sepa	arately numb	pered sheets attac	hed hereto			
CHID CHIEF DAYS OVER THE	TI	TLE OF THE IN	VENTION (280 characters n	nax)			
CHIP SHIELDING SYSTEM AN	D METHOD							
Direct all correspondence to:		CORRESP	ONDENCE	ADDRESS				
Customer Number OR	Customer Number				Place Customer Number Bar Code Label here			
Firm or Individual Name		ın, Welsh & Ka						
Address	120 S. Rive	erside Plaza, 2	2nd Floor					
Address	1							
City	Chicago		State	Illinois	ZIP	60606		
Country	USA		Telephone	312-655-1500	Fax	312-655-1501		
	ENCLOS	SED APPLICAT	TION PART	S (check all that	apply)			
Specification Number of Drawing(s) Number of Si	Pages	2		CD(s), Num				
Application Data Sheet, Se	,			Other (spec	cify)			
METHOD OF PAYMENT OF FI	LING FEES F	OR THIS PROV	/ISIONAL A	PPLICATION FO	R PATENT //	check one)		
A check or money order The Director is hereby a fees or credit any overpath Payment by credit card.	is enclosed to cuthorized to Department to Dep	o cover the filing harge filing posit Account N	g fees	23-0920]	FILING FEE AMOUNT (\$) \$160.00		
The invention was made by an a United States Government. No. Yes, the name of the U.S. Government.	gency of the l	Jnited States G			ct with an age	ency of the		
espectfully submitted,	·			Date	5/19/04			
GNATURE 'PED or PRINTED NAME L. Fr	iedman				ISTRATION N	NO. 37,135		
TEPHONE 312			Docket Number: 7251/92170					

USE ONLY FOR FILING A PROVISIONAL APPLICATION FOR PATENT

This collection of Information is required by 37 CFR 1.51. The information is used by the public to file (and by the PTO to process) a provisional application. Confidentiallity is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 8 hours to complete, including gathering, preparing, and submitting the complete provisional application to the PTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Mail Stop Provisional Application, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

P19LARGE/REV05

Complete if Known

PTO/SB/17 (10-03)

Approved for use through 07/31/2006. OMB 0851-0032

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

for TV 2004				Application Number			er				
for FY 2004			Ĺ	Filing Date 19 Mag			19 N	1ay 2004	y 2004		
Effective 10/01/2003. Patent fees are subject to annual revision.			on.	First Named Inventor John			ntor Johi	n Fleming W.	Fleming WALKER		
Applicant claims small entity status. See 37 CFR 1.27			27	Examiner Name							
			Art U	Init							
TOTAL	AMOUNT C	OF PAYMENT	(\$) \$16	0.00	Attor	ney Do	ocket i	No. 7251	1/92170		
MET	THOD OF	PAYMENT (ch	eck all that apply)				FE	E CALCU	LATION (co	ontinued)	
Check	Credit card	Comp. Com	ther None	3. A	DDITIC	DNAL			'		
Deposit Ac		Ly L	ш	Large Fee	Entity Fee	Small Fee	Entity Fee	-			
Deposit				Code	(\$)	Code	(\$)		e Description		Fee Paid
Account Number		23-0920		1051		2051			ate filing fee or		
Deposit	337	Joloh P. Moto	TAd	1052	50	2052	25	sheet	ate provisional	filing fee or cover	L
Account Name	W	elsh & Katz,	Lta.	1053	130	1053	130	Non - English	n specification		
The Director is	authorized to:	(check all that	l арріу)	1812	2,520	1812		,-	•	arte reexamination	
Charge fee(s	s) Indicated bet	ow Credit a	ny overpayments	1804	920*	1804	920*	Requesting paction	ublication of S	IR prior to Examine	f
Charge any	additonal fee(s) or any underpayme	nt of fee(s)	1805	1,840*	1805	1,840*	Requesting p	publication of S	IR after Examiner	
	-	ow, except for the fi	ling fee	1251	110	2251	55	action Extension for	reply within fir	rst month	
to the above-ider		ALCULATION	······	1252		2252	210		reply within se		
4 BASIC	FILING FE			1253	950	2253	475	Extension for	reply within th	ird month	
Large Entity				1254	1,480	2254	740	Extension for	reply within fo	ourth month	
Fee Fee	Fee Fee	Fee Description	Fee Paid	1255	2,010	2255	1,005	Extension for	reply within fit	fth month	
Code (\$) 1001 770	Code (\$) 2001 385	Utility filing fee	T CC T AIG	1401	330	2401	165	Notice of App	ceal		
1002 340		Design filing fee		1402	330	2402	165	Filing a brief	in support of a	n appeal	
1003 530		Plant filing fee		1403	290	2403	145	Request for o	oral hearing		
1004 770		Reissue filing fee		1451	1,510	1451	1,510	Petition to ins	stitute a public	use proceeding	
1005 160	2005 80	Provisional filing f	ee 160.00	1452	110	2452	55	Petition to re	vive - unavoida	able	
'	SUI	BTOTAL (1)	(\$) \$160.00	1453	1,330	2453	665		vive - unintenti	* 1	
2 FXTRA	CLAIM FE	ES FOR UTILIT	Y AND	1501	1,330	2501	665		ee (or reissue)	the state of the s	
2. 27(110-		Fe	e from	1502		2502	240	Design issue			
Total Claims	Extra CI		elow ree Paid	1503		2503	320	Plant issue for			
Independent	- 3**		= 0.00	1460		1460	130		he Commission		
Claims Multiple Depen	ident		=	1807		1807	50	_	ee under 37 Cf	T	
Large Entity			41	1808	180	1806	180	Statement	of Information I		
Fee Fee Code (\$)	Fee Fee Code (\$)	Fee Descri	ption	8021	40	8021	40		ach patent assi er of properties	gnment per propert	у
1202 18	2202 9	Claims in excess	of 20	1809	770	2809	385	Filing a subm	nission after fin		
1201 86	2201 43	Independent clain		1810	770	2810	385	(37 CFR § 1	litional inventio	on to be examined	
1203 290	2203 145		nt claim, if not paid			1	400	(37 CFR §	1.129(b))		
1204 86	2204 43	** Reissue indepe over original pa		1801		1		•		mination (RCE)	
1205 18	2205 9	** Reissue daims	in excess of 20	1802	. 900	1802	800	of a design a	expedited exam pplication	·······································	
l '		and over origina	al patent	Ott	ner fee (specify					
SUBTOTAL (2) (\$) \$0.00											· · · · · · · · · · · · · · · · · · ·
**or number previously paid, if greater; For Reissues, see above				*Re	duced t	y Basic	Filing	Fee Paid	SUBTO	TAL (3) (\$)	
SUBMITTED BY Complete (if applicable)											
Name (Print/T		L. Frie	dman		Registra).	37,135	Telephone	1	-1500
74.54				1	(Attorne)	wwgent)	—				
Signature Date 19 May 2004 WARNING: Information on this form may become public Credit card information should											

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on

not be included on this form. Provide credit card information and authorization on

This collection of information is required by 37 CFR 1.17 and 1.27. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

Patentee:

WALKER, John Fleming

Title:

CHIP SHIELDING SYSTEM AND METHOD

Serial No.:

Filing Date:

19 May 2004

Docket No.

7251/92170

Certificate of Express Mailing

Express Mail mailing label number EL 996734637 US

Date of Deposit: 19 May 2004

I hereby certify that this paper is being deposited with the United States Postal Service "Express Mail" Post Office to: Mail Stop Provisional Patent Application, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. This mailing includes Provisional Application Cover Sheet (1 pg); Fee Transmittal (1 pg) in duplicate; Check in the amount of \$160.00; Specification (8 pgs) and Drawings (2 sheets); Application Data Sheet (2 pgs); and return receipt postcard.

The person mailing this paper is:

John Austin Rembert

Typed or Printed Name of Person Mailing Paper of Fee

Signature of Person Mailing Paper or Fee

Application Data Sheet

Inventor Information

Inventor One Given Name:: John F

Family Name::

Postal Address Line One:: 1 M

City::

Country::

Postal or Zip Code::

Citizenship Country::

John Fleming

WALKER

1 Malyns Close Chinnor, Oxon

United Kingdom

OX39 4EW

United Kingdom

Correspondence Information

Name Line One:: Welsh & Katz, Ltd.

Name Line Two::

Address Line One::

L. Friedman
22nd Floor

Address Line Two:: 120 South Riverside Plaza

City:: Chicago

State or Province:: IL

Postal or Zip Code:: 60606 Telephone Number:: (312) 655-1500

Fax:: (312) 655-1501

Application Information

Title Line One:: CHIP SHIELDING SYSTEM AND METHOD

Total Drawing Sheets::

Application Type:: Provisional Docket Number:: 7251/92170

Representative Information

Registration Number One::	24,003
Registration Number Two::	22,839
Registration Number Three::	28,903
Registration Number Four::	27,429
Registration Number Five::	25,060
Registration Number Six::	22,053
Registration Number Seven::	27,466
Registration Number Eight::	29,434
Registration Number Nine::	29,054
Registration Number Ten::	29,381
Registration Number Eleven::	34,044
Registration Number Twelve::	27,600
Registration Number Thirteen::	34,137
Registration Number Fourteen:	38,110
Registration Number Fifteen::	39,724
Registration Number Sixteen:	39,021
Registration Number Seventeen:	37,963
Registration Number Eighteen:	37,135
Registration Number Nineteen:	40,604
Registration Number Twenty:	37,435
Registration Number Twenty-One:	45,195
Registration Number Twenty-Two:	40,687
Registration Number Twenty Three:	41,050

Assignee Information

Assignee Name:

NDS Limited

· Assignee Address:

One London Road

Staines, Middlesex TW18 4EX United Kingdom

CHIP SHIELDING SYSTEM AND METHOD

FIELD OF THE INVENTION

The present invention relates to protecting integrated circuit chips from invasive attack through the use of a shield.

BACKGROUND OF THE INVENTION

Security chips are of use to those wanting to protect information, data transmissions or value (typically monetary). These security chips protect data by storing it in secure memory or transmit data securely through the use of cryptography implemented on chip. There are many reasons for using these products including secure banking cards, secure access systems and secure personal identity systems. It is known in the art to protect these chips from invasive attacks whereby criminals and other agents attack the card to try to obtain, change or use secret information on the card.

One type of attack involves trying to place contacts onto internal chip nodes in order to read internal data traffic. This may be achieved by probing, using fine needles to break through the surface passivation to reach the fine metal tracks. Alternatively focused ion beam (FIB) may be used to deposit pads of metal onto the tracks for subsequent probing or bonding by wires. However it is achieved, measuring the signals on internal chip nodes represents an attack, and if successful this attack may render the chip and entire system on which it is based, insecure.

Shields to protect a chip from the above attacks exist at present; they are typically divided into two categories, active and passive. Passive shields are simple metal layers over all or part of the circuit and are designed to prevent viewing and probing. Passive shields may be removed by chemical, plasma or other techniques without changing the operation of the circuit. In other words, a passive shield works to deter attackers by making viewing more difficult initially, but will not actively defend itself against removal.

Active shields may look similar or may look more like a network of lines covering all or part of a circuit. If a line or part of the shield is removed,

30

5

15

20

severed or short-circuited to another line, the breach is detected and the chip halts some or all functions.

Active shields may still be breached using, for example, the following technique. An active shield line is identified as above the circuit element to be attacked. This shield line is bypassed using the ability of the FIB system previously mentioned. The bypass is in the form of a diversion track added in parallel to the original shield track. The original shield track may now be removed leaving the new bypass to fool the detection circuit. No circuit break is detected.

5

SUMMARY OF THE INVENTION

The present invention, in preferred embodiments thereof, comprises an active shield made in such a way that individual tracks are not visible by any normal microscopy technique. The tracks are preferably present in a layer of semiconductor material. The tracks preferably comprise doped regions separated by semi-insulating regions of either undoped material, or differently doped material. The tracks are doped sufficiently to allow conduction of electronic carriers. Between the tracks, the material, doped or undoped, is depleted of carriers. This region is rendered semi-insulating through the lack of intrinsic or extrinsic carriers, or through the trapping of such carriers. The conductive region is formed into tracks which form part of an active shield as described above. Most preferably, the conductive lines and the insulating regions between them are made in the same way and look identical to all analytical techniques. An attacker therefore does not know where to bypass the active shield lines.

15

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention will be understood and appreciated more fully from the following detailed description, taken in conjunction with the drawings in which:

Fig. 1 is a simplified pictorial illustration of an integrated circuit protected by chip shielding, constructed and operative in accordance with a preferred embodiment of the present invention; and

Fig. 2 is a simplified pictorial illustration of a top view of the integrated circuit of Fig. 1.

10

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

The present invention, in preferred embodiments thereof, provides a method to protect a security chip from invasive attacks. Preferably, a layer is added above the layers of the circuit to be protected from attack. The added layer may be made of polycrystalline silicon, as this material is commonly used in the manufacturing cycle of integrated circuits, but may alternatively be made of many other suitable materials. Any material whose conductivity can be materially changed without being visibly different would be a candidate for the material to be used in the added layer. The added layer is typically applied towards the end of the chip manufacturing process, and is applied above the normal circuit interconnect layers. The added layer may also be protected by a passivation layer, as is typically used in such integrated circuits.

10

15

20

25

30

The added layer is preferably implanted with dopants to allow conduction. In one preferred embodiment of the present invention dopants are selectively implanted in tracks corresponding to where the designer wants them placed. Dopants may be implanted in the material by high energy ion bombardment or by any other appropriate method.

In another preferred embodiment of the present invention utilizes either blanket bombardment of the layer with dopant ions or incorporation of the dopants during the growth of the layer. This latter approach will typically be achieved in the case of doped polysilicon, by CVD growth using silane gas for silicon growth and boron trichloride gas for dopant species.

However the growth and dopant incorporation is achieved, it must be done in such a way that the incorporated dopant atoms are not active. This means that the dopant atoms are not on designated sites as substitutes for the main material atoms. This means that the dopant atoms are interstitial, or between their normal, substitutional sites. This further means that the dopant atoms do not contribute carriers to conduction processes in the layer. This means that the material, as grown, is semi-insulating and does not conduct.

A further step in the creation of the shield layer is the selective activation of the dopants described above. The selective activation is typically achieved through an annealing process. This annealing process is effective if the

material is heated to a temperature close to (typically, within approximately 100 degrees C of) its melting point. In one preferred embodiment, the doped polysilicon is rapidly brought up to the annealing temperature by irradiation from a pulsed light source. The pulsed light source may be an infrared laser. The laser may be a YAG laser (Yttrium Aluminium Garnet, output wavelength 1064 nm). This laser may be driven in pulsed mode with a q-switch to limit the on-time to several nanoseconds or faster. The high power density during the pulse must be sufficient to anneal the dopants in that region of the material. In addition, the power density during the pulse must not be sufficient to ablate the material or cause damage to active circuit layers.

5

10

15

20

25

30

Conductive tracks are patterned into the layer by the annealing action. The laser, for example, may be scanned across the surface. The pattern of scanning is immaterial but may be raster scanning or following the semi-random path of a tracks path from start to end, or most efficiently, by alternate direction scanning (boustrephorous scanning) of the surface. The annealing will locally activate the dopants in the tracks required.

The annealing must be such that the conductive tracks are physically similar in all important respects to the semi-insulating material between the tracks. An attacker cannot "see", by normal analytical means, the tracks to be bypassed in an attack.

Reference is now made to Fig. 1, which is a simplified pictorial illustration of an integrated circuit protected by chip shielding, constructed and operative in accordance with a preferred embodiment of the present invention. This figure shows the basic construction of an integrated circuit with a silicon (single crystal) substrate on top of which are constructed gates and other active and passive circuit elements interconnected by networks of (typically) aluminium tracks. As these aluminium tracks are vulnerable to attack a layer of polysilicon is shown above them to illustrate the position of the protective shield layer.

Reference is now made to Fig. 2, which is a simplified pictorial illustration of a top view of the integrated circuit of Fig. 1. This figure shows a top down view of the protective shield layer. The serpentine track illustrates one method, as described above, of writing a serpentine conductive line in this

material. As described above, this can be achieved by scanning a pulsed infra-red laser over the areas to be annealed. The annealing activates the dopants in this region, allowing conduction along the track. The track may be connected to the underlying circuitry using, for example, tungsten plugs as vias.

It is appreciated that various features of the invention which are, for clarity, described in the contexts of separate embodiments may also be provided in combination in a single embodiment. Conversely, various features of the invention which are, for brevity, described in the context of a single embodiment may also be provided separately or in any suitable subcombination.

5

10

It will be appreciated by persons skilled in the art that the present invention is not limited by what has been particularly shown and described hereinabove. Rather the scope of the invention is defined only by the claims which follow:

What is claimed is:

CLAIMS

1.	Apparatus	substantially	as described	hereinabove.
----	-----------	---------------	--------------	--------------

- 2. Apparatus substantially as shown in the drawings.
- 3. A method substantially as described hereinabove.
- 10 4. A method substantially as shown in the drawings.

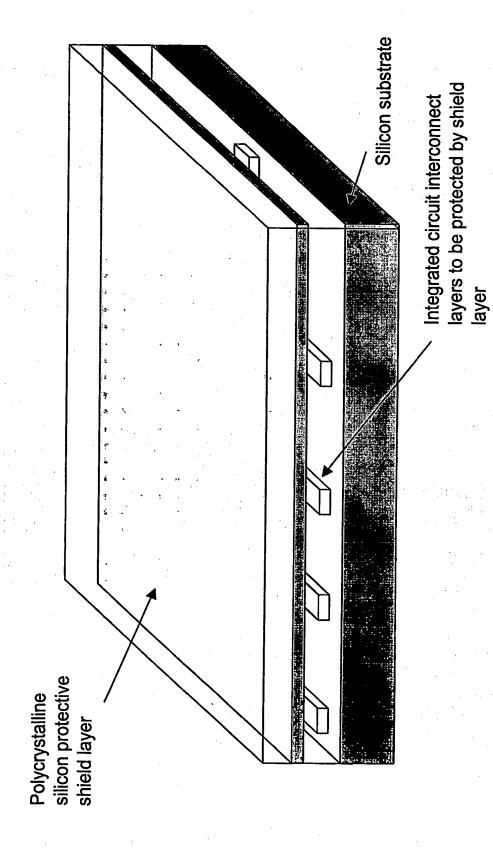


Fig.

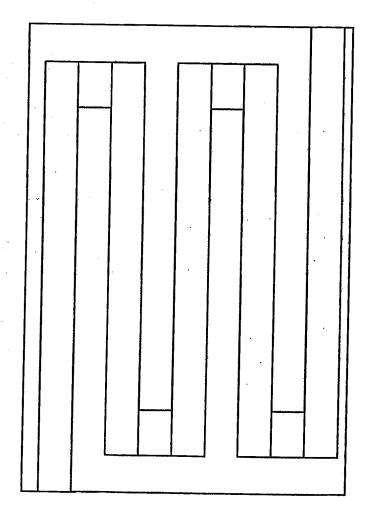


Fig. 2